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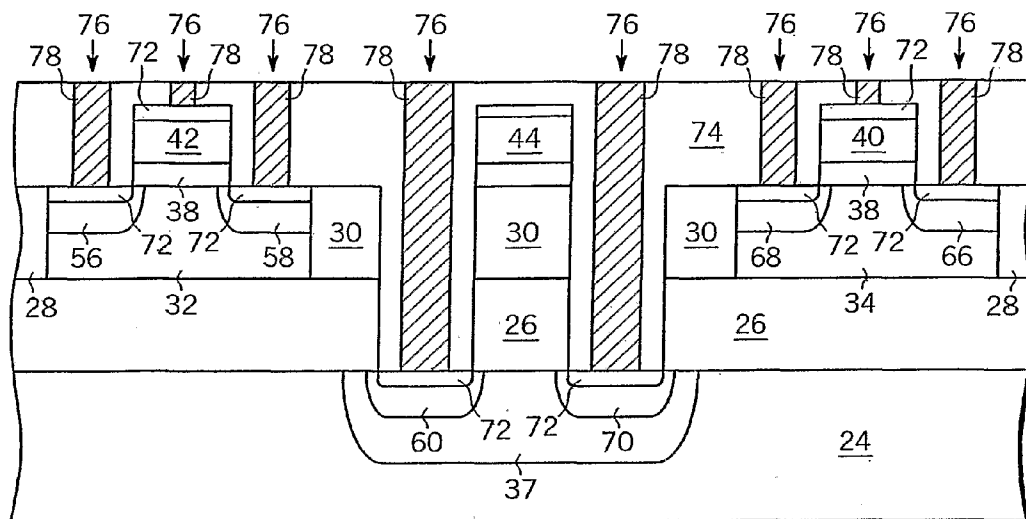
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(54) Title: METHOD FOR FABRICATING SOI DEVICE



20

(57) Abstract: A method is provided for fabricating a semiconductor on insulator (SOI) device [20]. The method includes, in one embodiment, providing a monocrystalline silicon substrate [24] having a monocrystalline silicon layer [22] overlying the substrate and separated therefrom by a dielectric layer [26]. A gate electrode material [39] is deposited and patterned to form a gate electrode [40, 42] and a spacer [44]. Impurity determining dopant ions [54, 56] are implanted into the monocrystalline silicon layer [22] using the gate electrode [40, 42] as an ion implant mask to form spaced apart source [56, 66] and drain [58, 68] regions in the monocrystalline silicon layer [22] and into the monocrystalline silicon substrate [24] using the spacer [44] as an ion implant mask to form spaced apart device regions [60, 70] in the monocrystalline substrate [24]. Electrical contacts [76] are then formed that contact the spaced apart device regions [60, 70].

WO 2006/124182 A1



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